



## Clean Version of Amended Claims

1           6. A method for cleaning a metal contact region of a semiconductor  
2       substrate, comprising exposing the metal contact region to hydrofluoric acid  
3       <sup>A3</sup> vapor and water vapor in a process chamber held at temperature and  
4       pressure conditions that are controlled to form on the substrate no more than  
5       a sub-monolayer of reactants and products produced by the vapor as the  
6       metal contact region is cleaned by the vapor.

1           9. The method of either of claims 7 or 8 wherein the process  
2       chamber temperature and pressure conditions are controlled to form on the  
3       substrate no more than a saturated monolayer of etch reactants and products  
4       produced by the vapor as the oxide is etched by the vapor.  
<sup>A4</sup>

1           10. The method of either of claims 7 or 8 wherein the process  
2       chamber temperature and pressure conditions are controlled to form on the  
3       substrate no more than a sub-monolayer of etch reactants and products  
4       produced by the vapor as the oxide is etched by the vapor.

1           15. The method of any of claims 12, 13, or 14 wherein the process  
2       <sup>AS</sup> chamber temperature and pressure conditions are controlled to form on the  
3       substrate no more than a sub-monolayer of etch reactants and products  
4       produced by the vapor as the oxide is etched by the vapor.

1           23. The method of claim 22 wherein the process chamber  
2       <sup>A6</sup> temperature and pressure conditions are controlled to form on the substrate  
3       no more than a saturated monolayer of etch reactants and products produced  
4       by the vapor as the oxide is etched by the vapor.

Ab<sup>1</sup>  
Cnt<sup>2</sup>  
3  
4

24. The method of claim 22 wherein the process chamber temperature and pressure conditions are controlled to form on the substrate no more than a sub-monolayer of etch reactants and products produced by the vapor as the oxide is etched by the vapor.